

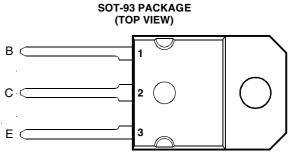
EN: This Datasheet is presented by the manufacturer.

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BDV64, BDV64A, BDV64B, BDV64C PNP SILICON POWER DARLINGTONS

BOURNS®

- Designed for Complementary Use with BDV65, BDV65A, BDV65B and BDV65C
- 125 W at 25°C Case Temperature
- 12 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 5 A



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BDV64		-60		
Collector-base voltage ($I_E = 0$)	BDV64A	N/	-80	V	
	BDV64B	V _{CBO}	-100		
	BDV64C		-120		
	BDV64		-60		
Collector-emitter voltage ($I_B = 0$)	BDV64A	N/	-80	V	
	BDV64B	V _{CEO}	-100		
	BDV64C		-120		
Emitter-base voltage	V _{EBO}	-5	V		
Continuous collector current			-12	Α	
Peak collector current (see Note 1)			-15	Α	
Continuous base current			-0.5	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3.5	W	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			260	°C	

NOTES: 1. This value applies for $t_p \leq 0.1$ ms, duty cycle $\leq 10\%$

2. Derate linearly to $150^{\circ}C$ case temperature at the rate of 0.56 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST	CONDITIONS		MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 4)	BDV64 BDV64A BDV64B BDV64C	-60 -80 -100 -120			v
I _{CEO}	Collector-emitter cut-off current	$V_{CB} = -30 V$ $V_{CB} = -40 V$ $V_{CB} = -50 V$ $V_{CB} = -60 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BDV64 BDV64A BDV64B BDV64C			-2 -2 -2 -2	mA
I _{CBO}	Collector cut-off current	$\begin{array}{rrrr} V_{CB} = & -60 \ V \\ V_{CB} = & -80 \ V \\ V_{CB} = & -100 \ V \\ V_{CB} = & -120 \ V \\ V_{CB} = & -30 \ V \\ V_{CB} = & -30 \ V \\ V_{CB} = & -50 \ V \\ V_{CB} = & -60 \ V \end{array}$	$I_{E} = 0$	$T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$ $T_{C} = 150^{\circ}C$	BDV64 BDV64A BDV64B BDV64C BDV64 BDV64A BDV64B BDV64C			-0.4 -0.4 -0.4 -2 -2 -2 -2 -2	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	l _C = 0					-5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = -4 V	I _C = -5 A	(see Notes 4 and 5)		1000			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -20 mA	I _C = -5 A	(see Notes 4 and	15)			-2	V
V _{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -5 A	(see Notes 4 and 5)				-2.5	V
V _{EC}	Parallel diode forward voltage	I _E = -10 A	l _B = 0	(see Notes 4 and	15)			-3.5	V

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu$ s, duty cycle $\leq 2\%$.

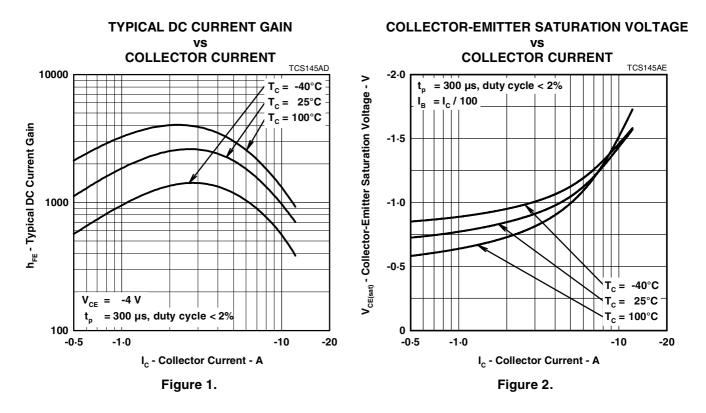
5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

	PARAMETER		ТҮР	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1	°C/W
R_{\thetaJA}	Junction to free air thermal resistance			35.7	°C/W



TYPICAL CHARACTERISTICS



BASE-EMITTER SATURATION VOLTAGE vs **COLLECTOR CURRENT** TCS145AF -3.0 = -40°C $v_{\text{BE(sat)}}$ - Base-Emitter Saturation Voltage - V т, 25°C T_ = -2.5 100°C -2.0 -1.0 -1.5 -0.5 I_B = I_c / 100 = 300 μ s, duty cycle < 2% t 0 -0.5 -1.0 -10 -20 I_c - Collector Current - A Figure 3.

PRODUCT INFORMATION

JUNE 1993 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

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THERMAL INFORMATION

